

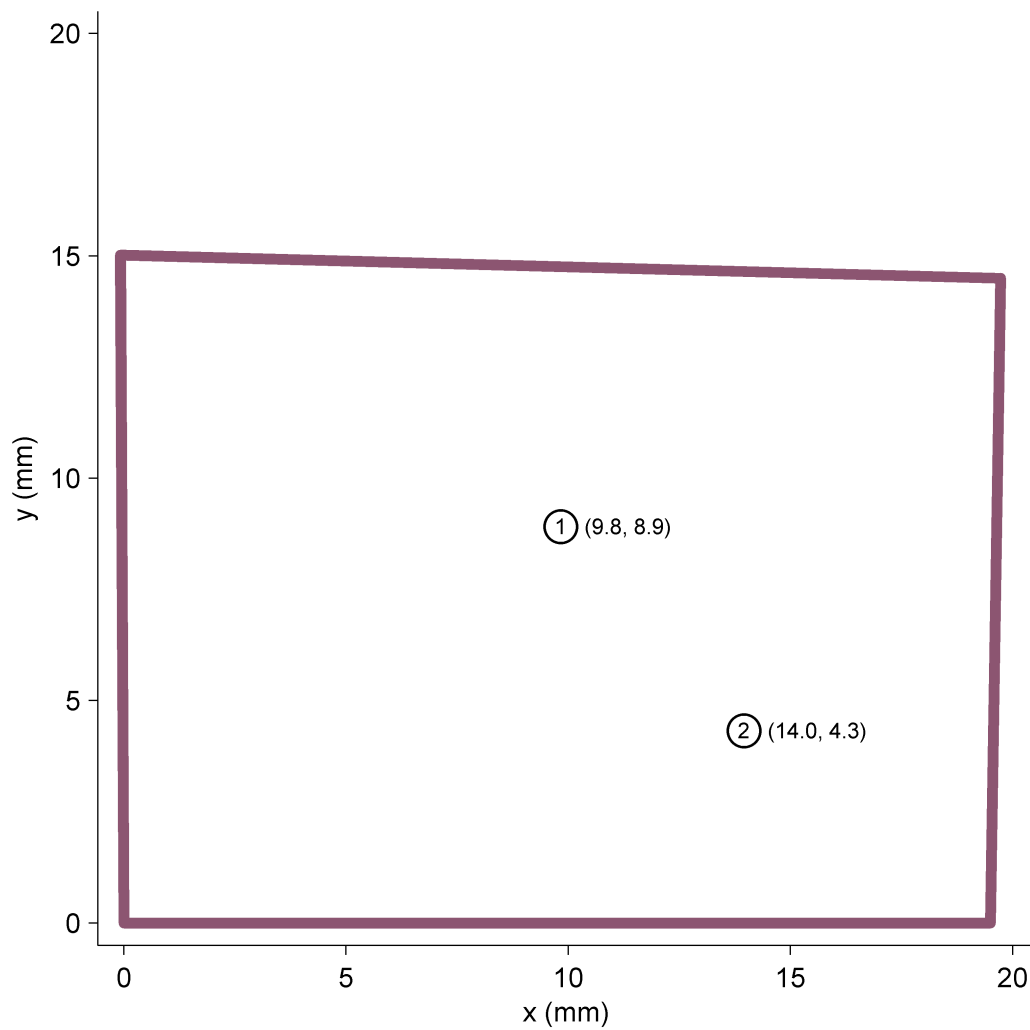


Sample S5519 Datasheet

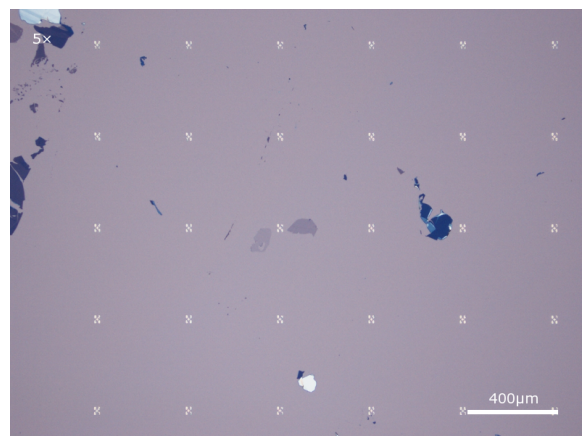
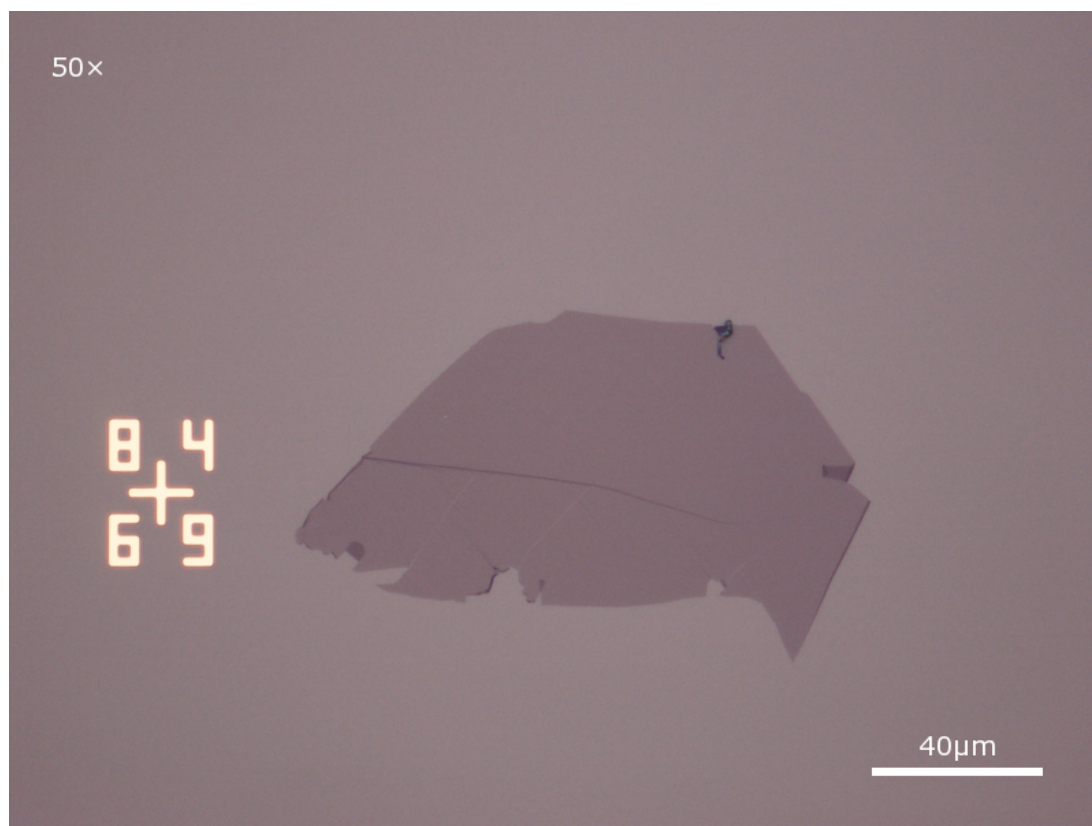
Parent Wafer

Supplier	IDB Technologies Ltd.
Diameter	100mm
Si Orientation	<100>
Si Thickness	525 μm
Si Doping	N-type, arsenic
Resistivity	0.001-0.010 Ωcm
Oxide	90 nm dry thermal oxide

Substrate Map



Flake 1 of 2: $x=9.8\text{mm}$, $y=8.9\text{mm}$, $>5000\text{ }\mu\text{m}^2$ bilayer flake with crease.



Flake 2 of 2: x=14.0mm, y=4.3mm, >1800 μm^2 monolayer flake

